

3DG182

NPN Silicon High Reverse Voltage High Frequency



Middle Power Transistor

Features:

1. Using epitaxy planar technology structure. High working frequency. Metallic packaging.
2. Small volume, light weight, easy installation.
3. Use for high frequency oscillation, high frequency small signal amplification, low power source adjustment circuit.
4. Quality Class: GS, G. Implementation of standards: QZJ840611

TECHNICAL DATA:

(Ta = 25°C)

Parameter name	Symbols	Unit	Specifications										Test Condition
			A	B	C	D	E	F	G	H	I	J	
Total Dissipation	P _{tot}	mW	700										Ta=25°C
Max. Collector Current	I _{CM}	mA	300										
Junction Temperature	T _{jm}	°C	175										
Storage Temperature	T _{stg}	°C	-55~+175										
C-B Breakdown Voltage	V _{(BR)CBO}	V	60	100	140	180	220	60	100	140	180	220	I _C =0.1mA
C-E Breakdown Voltage	V _{(BR)CEO}	V	60	100	140	180	220	60	100	140	180	220	
E-B Breakdown Voltage	V _{(BR)EBO}	V	5										I _E =0.1mA
Collector- Emitter Saturation Voltage Drop	V _{CE(sat)}	V	1.0										I _C =200mA, I _B =20mA
Base- Emitter Saturation Voltage Drop	V _{BE(sat)}	V	1.2										
C-B Leakage Current	I _{CBO}	uA	1.0										V _{CB} =30V
C-E Leakage Current	I _{CEO}	uA	2.0										V _{CE} =30V
E-B Leakage Current	I _{EBO}	uA	1.0										V _{EB} =1.5V
DC Current Gain	h _{FE}		25~180										V _{CE} =2V, I _C =200mA
Transition frequency	f _T	MHz	50					100					V _{CE} =10V, I _C =20mA f=30MHz

h_{FE} Colored:

Color	Orange	Yellow	Green	Blue	Purple
h _{FE}	25~40	40~55	55~80	80~120	120~180

Outline and Dimensions: